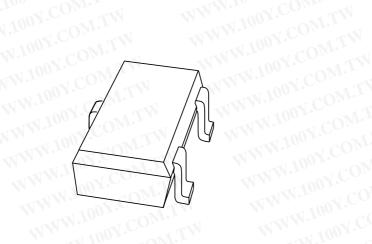
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WWW.100Y.COM.TW **PBSS4140U** 40 V low V_{CEsat} NPN transistor

Product data sheet Supersedes data of 2001 Mar 27 WWW.100Y.COM.TW 2001 Jul 13



40 V low V_{CEsat} NPN transistor

PBSS4140U

FEATURES

- · Low collector-emitter saturation voltage
- High current capabilities.
- Improved device reliability due to reduced heat generation.
- Enhanced performance over SOT231A general purpose packaged transistors.

APPLICATIONS

- · General purpose switching and muting
- · LCD backlighting
- · Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT323 plastic package. PNP complement: PBSS5140U.

MARKING

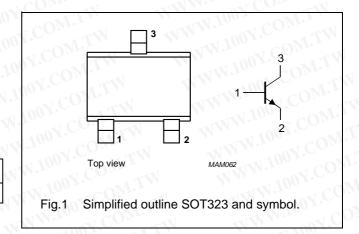
TYPE NUMBER	MARKING CODE
PBSS4140U	41t

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	40	V
I _{CM}	peak collector current	2	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
M. TIN	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	O_{M}	40	V
V _{CEO}	collector-emitter voltage	open base	CO_{M-1}	40	V
V _{EBO}	emitter-base voltage	open collector	-coM.	5	V
I _C	collector current (DC)	MITW WWW. 100	N.O.	11	Α
I _{CM}	peak collector current	WWW.	ON.CO	2	A
I _{BM}	peak base current	COM. WIN WINN.	TY.CO	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	- VCO	250	mW
	W 100	T _{amb} ≤ 25 °C; note 2	100 >	350	mW
T _{stg}	storage temperature	T. OW.TW	-65	+150	°C
Tj	junction temperature	DY.C TITT	_	150	°C
T _{amb}	operating ambient temperature	ON.COM	-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm.

NXP Semiconductors Product data sheet

40 V low V_{CEsat} NPN transistor

PBSS4140U

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a} ther	thermal resistance from junction to	in free air; note 1	500	K/W
ambient		in free air; note 2	357	K/W

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
I _{CBO}	collector-base cut-off	V _{CB} = 40 V; I _C = 0	-WW	14.30	100	nA	
	current	V _{CB} = 40 V; I _C = 0; T _{amb} = 150 °C		A. In.	50	μΑ	
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0$	- 1	W.M.T.	100	nA	
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0$	- <	A SNA	100	nA	
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	300	HWW	Tooy.	CO_{2s}	
	M.1001. COM.17	V _{CE} = 5 V; I _C = 500 mA	300	= 11/1	900	COM	
	W 100Y. COM.TW	V _{CE} = 5 V; I _C = 1 A	200		14.100°	7 (0)	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 1 mA	17	- 1/1	200	mV	
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	Ψ.	- 11	250	mV	
		I _C = 1 A; I _B = 100 mA	-W	- 1	500	mV	
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	- W	260	<500	mΩ	
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA	W.T.M	_	1.2	V 1005	
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 1 A	- TT	_	1.1	V 100	
f _T	transition frequency	$I_C = 50 \text{ mA}$; $V_{CE} = 10 \text{ V}$; $f = 100 \text{ MHz}$	150	4	- 1111	MHz	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	$O_{Mr.}$	- 	10	pF	

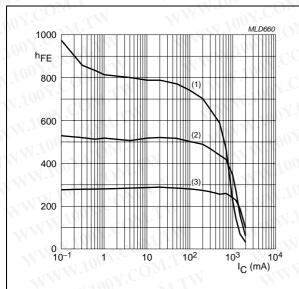
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$ WWW.100Y.COM.TW

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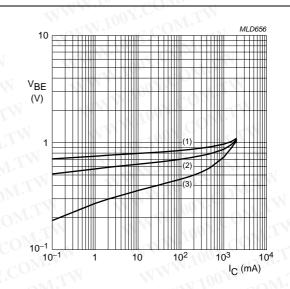
PBSS4140U



 $V_{CE} = 5 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \,^{\circ}C$.

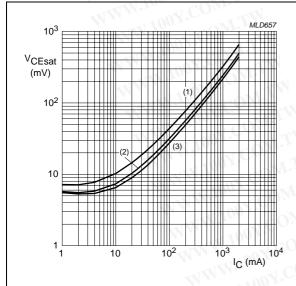
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

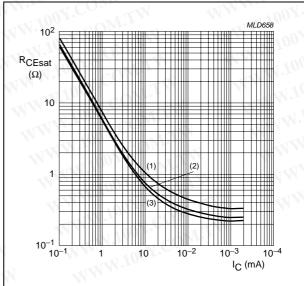
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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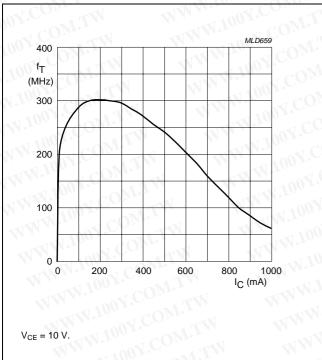
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Transition frequency as a function of collector current; typical values.

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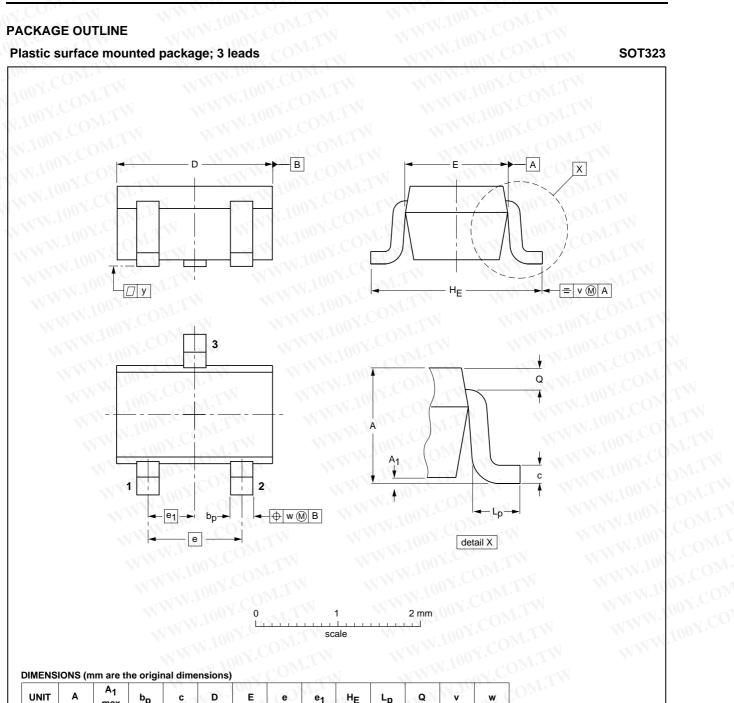
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



UNIT	Α	A ₁ max	bp	C	D	E	е	e ₁	HE	Lp	Q	v	w.
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2	0.45 0.15	0.23 0.13	0.2	0.2
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OUTLINE		REFERENCES			REFERENCES EUROPEAN ISSUE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION			
SOT323			SC-70			97-02-28		

6

NXP Semiconductors Product data sheet

40 V low V_{CEsat} NPN transistor

PBSS4140U

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION			
Objective data sheet	Development	This document contains data from the objective specification for product development.			
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.			
Product data sheet	Production	This document contains the product specification.			

Notes

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2001 Jul 13 7